

1N4001 SERIES

1.0 Amp Silicon Rectifier Diodes

Major Ratings and Characteristics

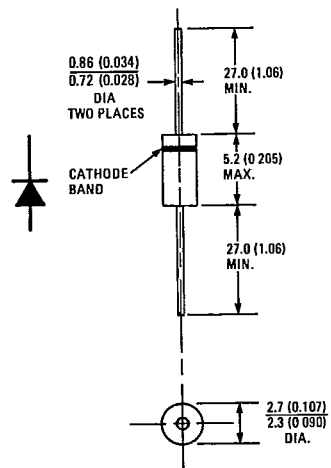
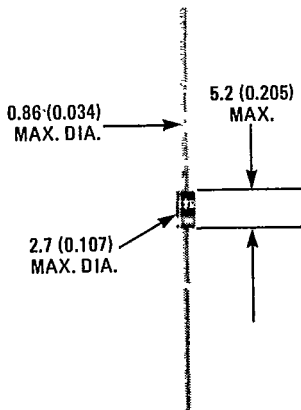
	1N4001	Units
$I_F(AV)$	1.0 *	A
@ Max. T_A	75 *	$^{\circ}C$
I_{FSM}		
@ 50 Hz	28.7	A
@ 60 Hz	30 *	A
$I^2\sqrt{t}$	58.1	$A^2\sqrt{s}$
T_J Range	-65 to 175 *	$^{\circ}C$
VRRM Range	50 to 1000 *	V

Description/Features

- Economical 1 ampere general purpose diode for industrial application
- Molded epoxy DO-204AL case style
- Low forward voltage drop and high surge rating
- Excellent reliability

*JEDEC registered value.

CASE STYLE AND DIMENSIONS



Case Style DO-204AL
 Dimensions in Millimeters and (Inches)

VOLTAGE RATINGS

Part Number	V_{RRM} – Max. Repetitive Peak Reverse Voltage (V)	$V_R(RMS)$ – Max. RMS Reverse Voltage (V)	V_R – Max. DC Blocking Voltage (V)
	T = –65 to 175°C	T = –65 to 175°C	T = –65 to 165°C
1N4001	50*	35	50*
1N4002	100*	70	100*
1N4003	200*	140	200*
1N4004	400*	280	400*
1N4005	600*	420	600*
1N4006	800*	560	800*
1N4007	1000*	700	1000*

ELECTRICAL SPECIFICATIONS

		1N4001	Units	Conditions
$I_F(AV)$	Max. average forward current	1.0*	A	Half sine wave conduction ①, double side cooled.
	@ Max. T_A	75*	°C	
I_{FSM}	Max. peak one cycle, non-repetitive surge current	28.7	A	Half cycle 50 Hz sine wave or 6 ms rectangular pulse. Following any rated load condition, and with rated V_{RRM} reapplied.
		30*		
$I^2\sqrt{t}$	Max. $I^2\sqrt{t}$ for fusing ①	58.1	$A^2\sqrt{s}$	t = 0.1 to 10 ms with V_{RRM} following surge = rated V_{RRM} .
V_{FM}	Max. peak forward voltage	1.1*	V	$T_A = -65^\circ\text{C}$ to 75°C , $I_F = 1 \text{ Adc}$
		1.6*	V	$T_A = -65^\circ\text{C}$ to 75°C , $I_F(AV) = 1 \text{ A}$ (3.14A peak)
I_R	Max. dc reverse current	10*	μA	$T_A = 25^\circ\text{C}$ $V_R = \text{Rated } V_R$.
		50*	μA	$T_A = 100^\circ\text{C}$
$I_R(AV)$	Max. average reverse current	30*	μA	$T_A = 75^\circ\text{C}$, $I_F(AV) = 1 \text{ A}$, $V_{RRM} = \text{rated } V_{RRM}$

THERMAL-MECHANICAL SPECIFICATIONS

T_J	Max. operating junction temperature range	–65* to 175*	°C
T_{stg}	Max. storage temperature range	–65* to 200*	°C
wt	Approximate weight	0.33 (0.012)	g (oz)
	Case Style	DO-204AL (DO-41)	

① T_L is measured 8.7 mm (0.344 in.) to 9.5 mm (0.375 in.) from device case.

① I^2t for time $t_x = I^2\sqrt{t} \cdot \sqrt{t_x}$.

*JEDEC registered values.

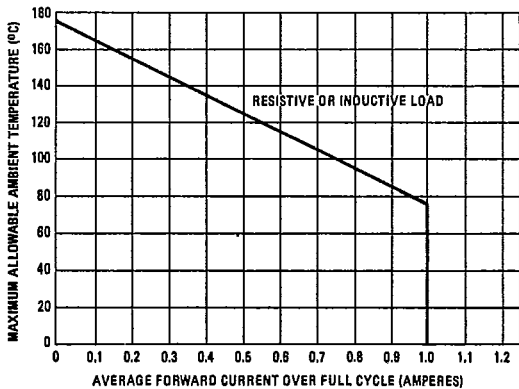


Fig. 1 – Average Forward Current Vs. Maximum Allowable Ambient Temperature

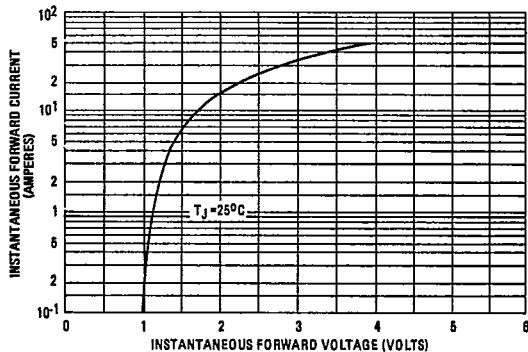


Fig. 2 – Maximum Forward Voltage vs. Forward Current

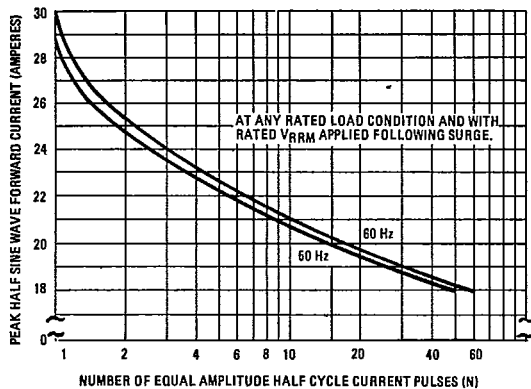


Fig. 3 – Maximum Non-Repetitive Surge Current Vs. Number of Current Pulses